

**SESSION 2 –TAPA I**  
**High-Speed Data Converters**

Wednesday, June 18, 10:25 a.m.

Chairpersons: B. Nauta, University of Twente  
M. Nagata, Kobe University

**2.1 – 10:25 a.m.**

**A Low Power 6-bit Flash ADC with Reference Voltage and Common-Mode Calibration**, C.-Y. Chen, M. Le, K.Y. Kim, Broadcom Corporation, USA

A low power 6-bit ADC that uses reference voltage and common-mode calibration to improve linearity and reduce power dissipation is presented. The ADC occupies 0.13mm<sup>2</sup> in 65nm CMOS. The ADC dissipates 4mW at 100MS/s and 12mW at 800MS/s from a 1.2V supply.

**2.2 – 10:50 a.m.**

**A 7.6 mW 1.75 GS/s 5 Bit Flash A/D Converter In 90nm Digital CMOS**, B. Verbruggen, P. Wambacq, M. Kuijk\*, G. Van der Plas, IMEC, \*Vrije Universiteit, Belgium

A 5 bit 1.75 GS/s flash ADC is realized in 90 nm CMOS. It uses a comparator array with built-in imbalance and offset calibration to lower power consumption. The SNDR is 30.9 dB at low frequencies and gradually degrades to 28.2 dB at 2 GHz. The ADC occupies 280μm by 110μm and draws only 7.6 mA from a 1 V supply yielding an energy efficiency of 0.15 pJ/conversion step.

**2.3 – 11:15 a.m.**

**A 6-bit 5-GSample/s Nyquist A/D Converter in 65nm CMOS**, M. Choi, J. Lee, J. Lee, H. Son, Samsung Advanced Institute of Technology, Korea

A 6-bit Nyquist A/D converter (ADC) that converts at 5 GHz is reported. Using a wideband track-and-hold amplifier, array averaging, reset switches on analog signal paths, and phase-adjusted clocking for cascaded comparators, a 6-bit flash ADC achieves better than 5 effective bits for input frequencies up to 2.5 GHz at 5 GSample/s. This ADC does not rely on time interleaving, digital calibration, and post data processing for its dynamic performance. This ADC consumes about 320mW from 1.3 V at 5 GSample/s. The chip occupies 0.3mm<sup>2</sup> active area, fabricated in 65nm CMOS.

**2.4 – 11:40 a.m.**

**A 10.3GS/s 6bit (5.1 ENOB at Nyquist) Time-Interleaved/Pipelined ADC Using Open-Loop Amplifiers and Digital Calibration in 90nm CMOS**, A. Nazemi, C. Grace, L. Lewyn, B. Kobeissy, O. Agazzi, P. Voois, C. Abidin, G. Eaton, M. Kargar, C. Marquez, S. Ramprasad, F. Bollo\*, V. Posse, S. Wang, G. Asmanis, ClariPhy Communications Inc., USA, \*ClariPhy, Argentina

A 10.3GS/s ADC with 5GHz input BW and 6 bit resolution in 90nm CMOS is presented. The architecture is based on an 8 way interleaved/ pipelined ADC using open-loop amplifiers and digital calibration. The measured performance is 5.8 ENOB (36.6dB SNDR) for a 100MHz input signal and 5.1 ENOB (32.4dB SNDR) for a 5GHz input (Nyquist) with phase offset correction across the interleaved array.